

Title: METHOD OF FABRICATING CMOS INVERTER AND
INTEGRATED CIRCUITS UTILIZING STRAINED SILICON
SURFACE CHANNEL MOSFETS

Inventors: Eugene A. Fitzgerald et al.

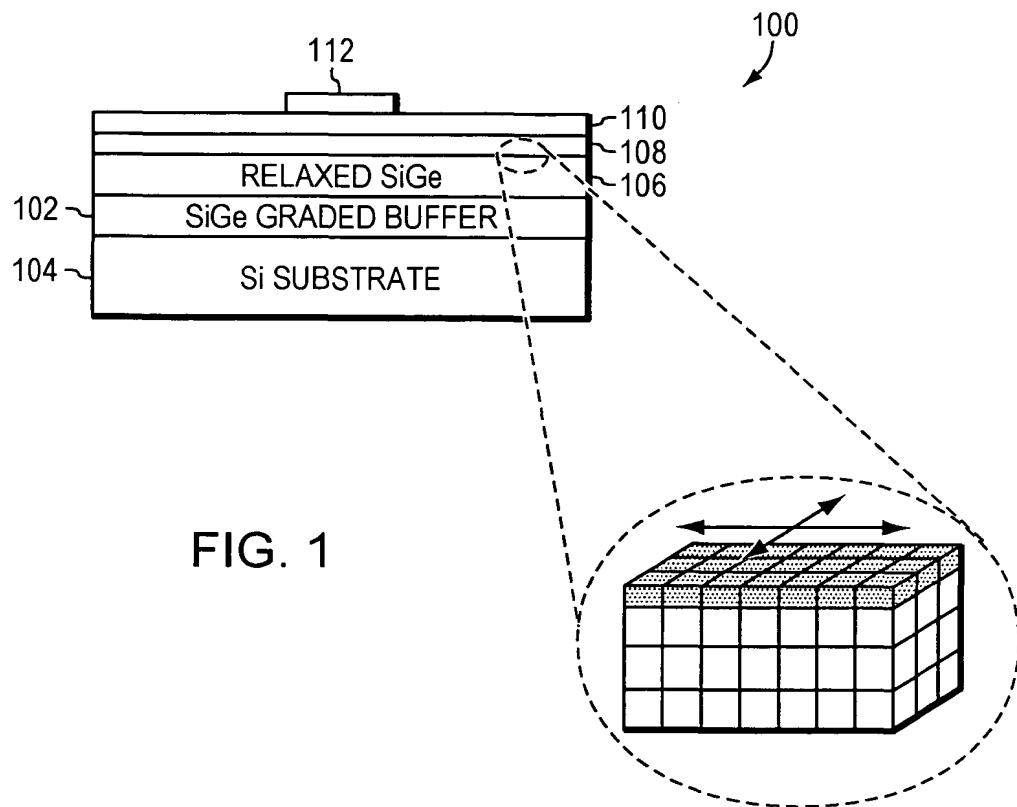
Serial No. *Not yet assigned*

Atty Docket No. ASC-044C1

Atty/Agent: Steven J. Frank/kb

Express Mail Label No. EV192309385US

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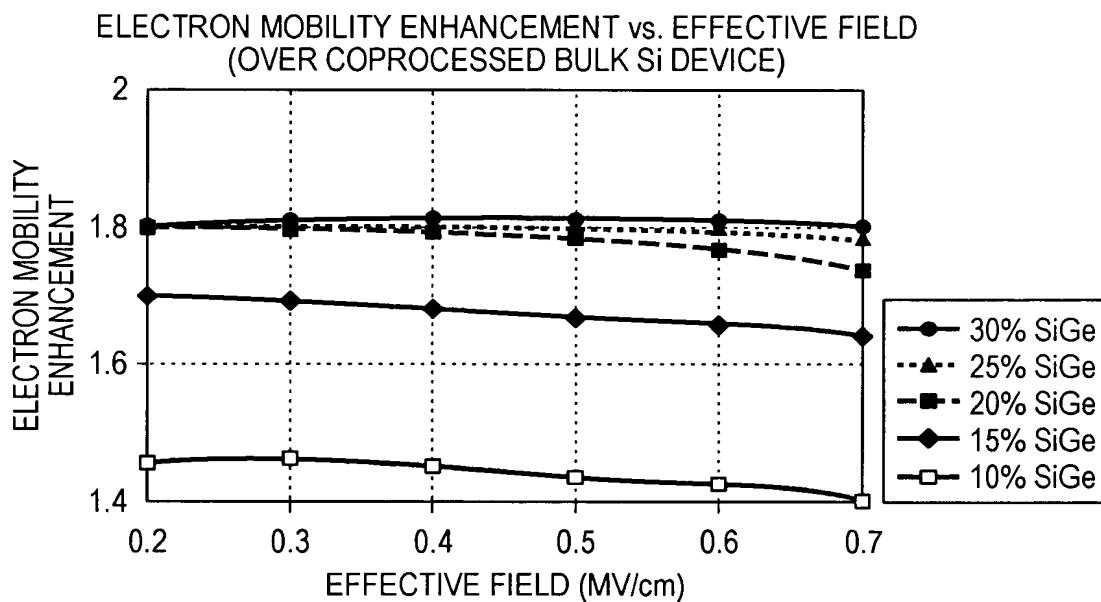


FIG. 2A

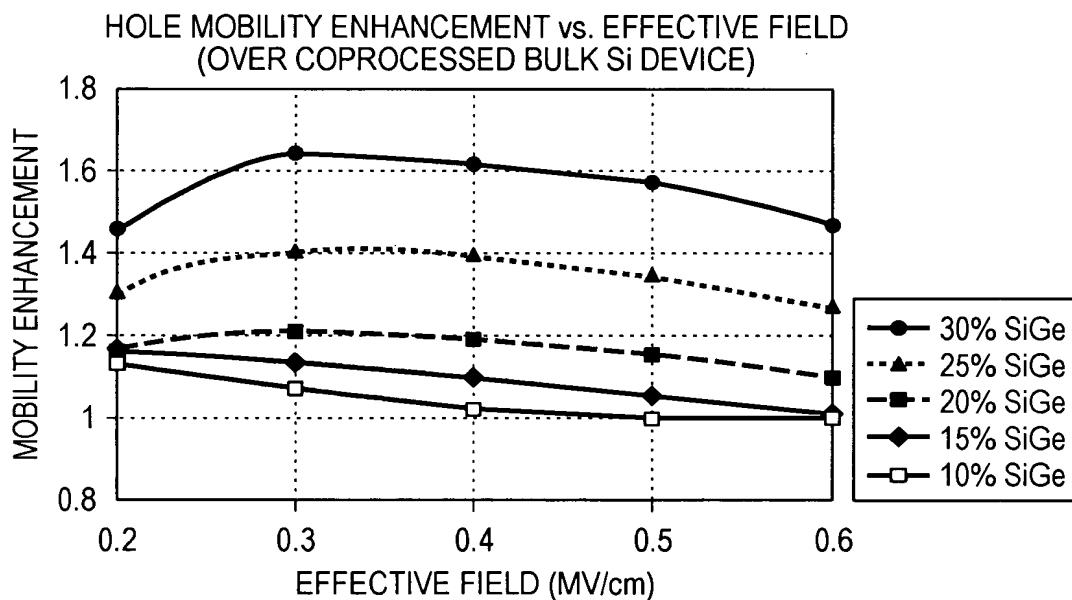


FIG. 2B

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TYPE OF SURFACE	AVERAGE ROUGHNESS (nm)
AS-GROWN GRADED COMPOSITION RELAXED SiGe	7.9
PLANARIZED SiGe	0.57
REGROWTH SiGe	-0.6

FIG. 3

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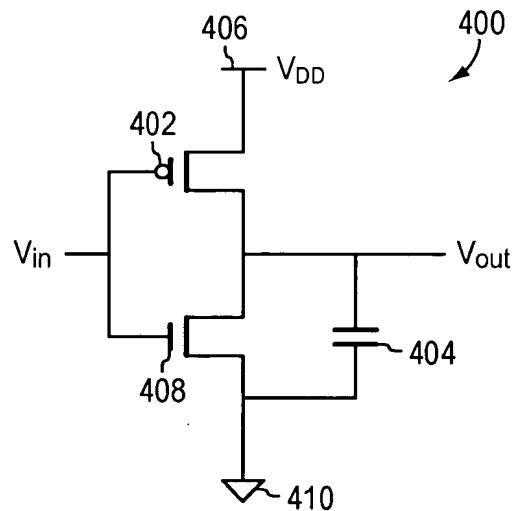


FIG. 4

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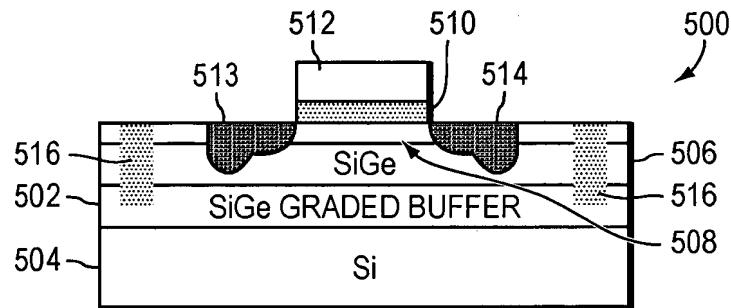


FIG. 5A

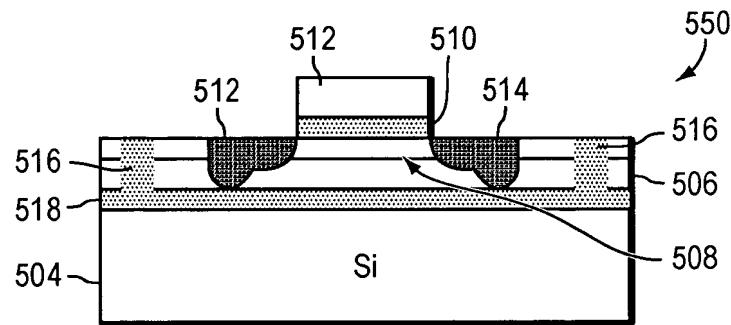


FIG. 5B

Title: METHOD OF FABRICATING CMOS INVERTER AND
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	n ENHANCEMENT	p ENHANCEMENT
Si _{0.8} Ge _{0.2}	1.75	1
Si _{0.7} Ge _{0.3}	1.8	1.4

FIG. 6

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	BULK SILICON	STRAINED-Si ON 20% SiGe: HIGH SPEED	STRAINED-Si ON 30% SiGe: HIGH SPEED	STRAINED-Si ON 20% SiGe: LOW POWER	STRAINED-Si ON 30% SiGe: LOW POWER
n ENHANCEMENT	1	1.75	1.8	1.75	1.8
p ENHANCEMENT	1	1	1.4	1	1.4
W _p (μm)	5.4	5.4	5.4	5.4	5.4
W _n (μm)	1.8	1.8	1.8	1.8	1.8
L _n ,L _p (μm)	1.2	1.2	1.2	1.2	1.2
C _L (fF)	32	32	32	32	32
V _{DD} (V)	5	4.7	4.4	4.3	3.8
NM _H (V)	2.053	2.218	1.949	2.037	1.682
NM _L (V)	2.067	1.654	1.721	1.542	1.504
t _{pHL} (psec)	211.3	133.7	141.6	152.2	180.1
t _{pLH} (psec)	195.8	220.0	173.3	254.8	226.9
t _p (psec)	203.5	176.9	157.4	203.5	203.5
POWER (mW)	3.93	3.93	3.93	2.87	2.21
% SPEED INCREASE	-	15.1%	29.3%	-	-
% POWER REDUCTION	-	-	-	27.0%	43.7%

FIG. 7

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	BULK SILICON	STRAINED-Si ON 20% SiGe: CONSTANT V_{DD}	STRAINED-Si ON 30% SiGe: CONSTANT V_{DD}	STRAINED-Si ON 20% SiGe: HIGH SPEED SYMMETRICAL INVERTER	STRAINED-Si ON 30% SiGe: HIGH SPEED SYMMETRICAL INVERTER	STRAINED-Si ON 20% SiGe: LOW POWER SYMMETRICAL INVERTER	STRAINED-Si ON 30% SiGe: LOW POWER SYMMETRICAL INVERTER
n ENHANCEMENT	1	1.75	1.8	1.75	1.8	1.75	1.8
p ENHANCEMENT	1	1	1.4	1	1.4	1	1.4
W_p (μm)	5.4	5.4	5.4	9.45	6.94	9.45	6.94
W_n (μm)	1.8	1.8	1.8	1.8	1.8	1.8	1.8
L_n, L_p (μm)	1.2	1.2	1.2	1.2	1.2	1.2	1.2
C_L (fF)	32	32	32	32	32	32	32
V_{DD} (V)	5	5	5	4.3	4.2	3.5	3.5
NM_H (V)	2.053	2.376	2.198	1.782	1.770	1.5018	1.4796
NM_L (V)	2.067	1.751	1.923	1.794	1.781	1.5101	1.4876
t_{PHL} (psec)	211.3	120.7	117.4	152.0	149.5	204.4	204.1
t_{PLH} (psec)	195.8	195.8	139.9	145.4	143.3	202.6	202.9
t_p (psec)	203.5	158.3	128.6	148.7	146.4	203.5	203.5
POWER (mW)	3.93	5.06	6.22	3.93	3.93	1.95	1.89
% SPEED INCREASE	-	28.6%	58.3%	36.9%	39.0%	-	-
% POWER REDUCTION	-	-	-	-	-	50.4%	52.0%

FIG. 8

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	BULK SILICON	STRAINED-Si ON 20% SiGe: HIGH SPEED	STRAINED-Si ON 30% SiGe: HIGH SPEED	STRAINED-Si ON 20% SiGe: LOW POWER	STRAINED-Si ON 30% SiGe: LOW POWER
n ENHANCEMENT	1	1.75	1.8	1.75	1.8
p ENHANCEMENT	1	1	1.4	1	1.4
W_p (μm) -	3.11	4.12	3.53	4.12	3.53
W_n (μm)	1.8	1.8	1.8	1.8	1.8
L_n, L_p (μm)	1.2	1.2	1.2	1.2	1.2
C_L (fF)	22.5	26.7	24.2	26.7	24.2
V_{DD} (V)	5	4.5	4.3	4.4	3.8
NM_H (V)	2.370	2.275	2.123	2.220	1.872
NM_L (V)	1.756	1.485	1.511	1.458	1.371
t_{pHL} (psec)	148.4	117.3	109.3	121.5	132.4
t_{pLH} (psec)	238.5	254.8	204.9	265.3	254.4
t_p (psec)	193.4	186.0	157.1	193.4	193.4
POWER (mW)	2.90	2.90	2.90	2.66	1.83
% SPEED INCREASE	-	4.0%	23.1%	-	-
% POWER REDUCTION	-	-	-	8.4%	37.1%

FIG. 9

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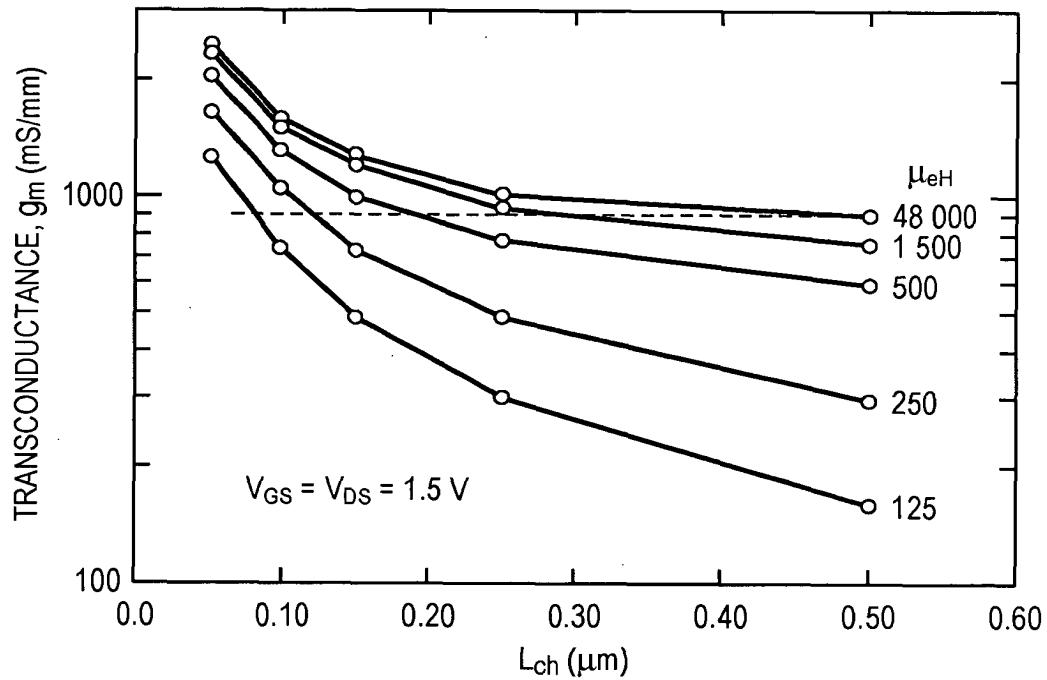


FIG. 10

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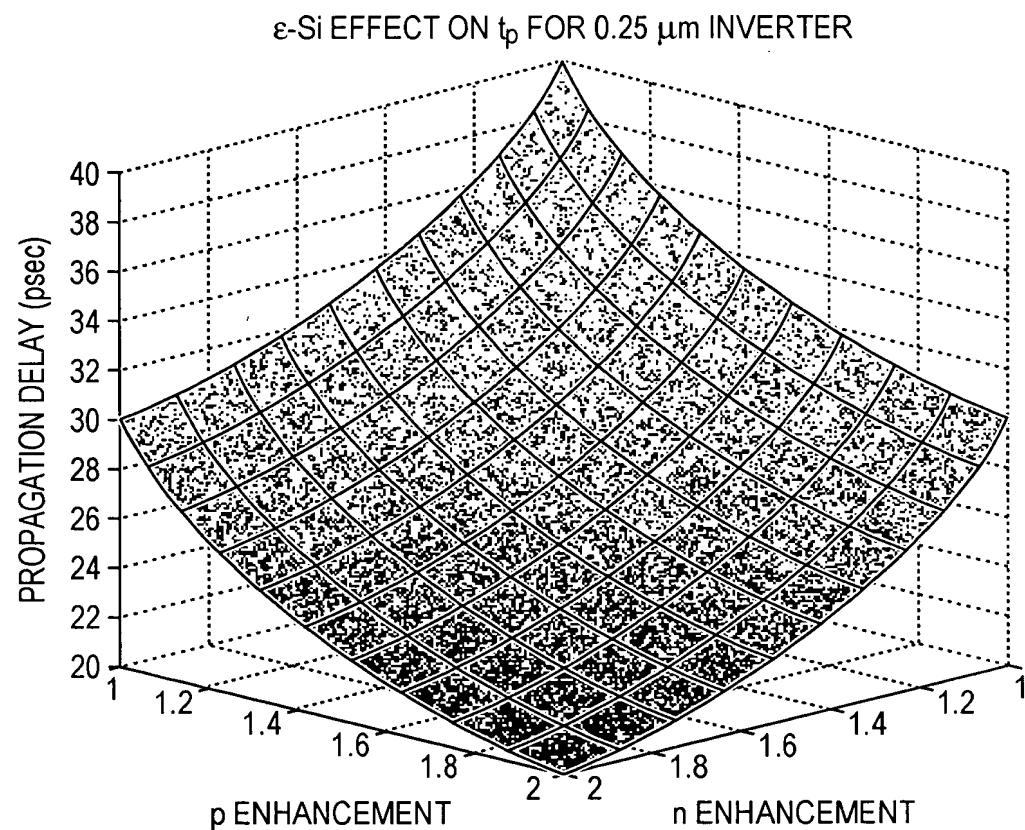


FIG. 11

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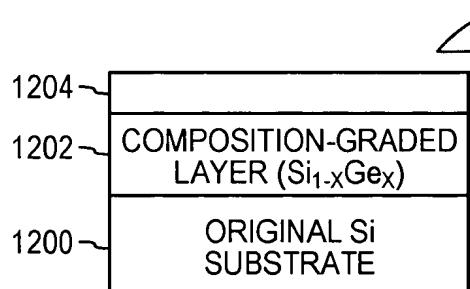


FIG. 12A

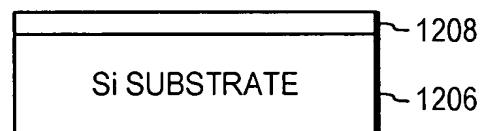


FIG. 12B

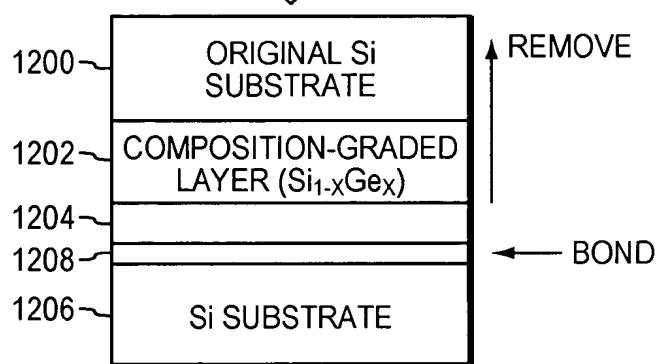


FIG. 12C

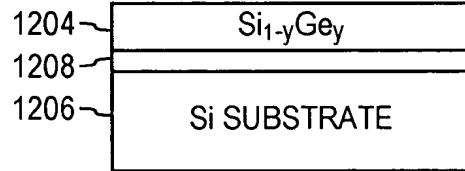


FIG. 12D

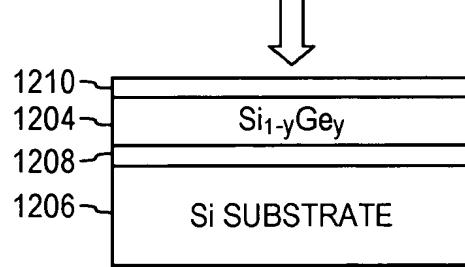


FIG. 12E

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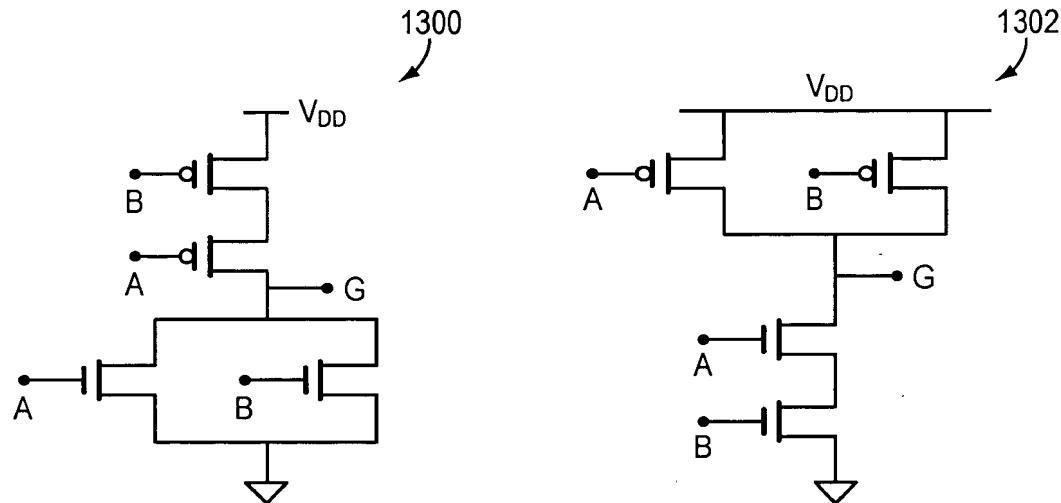


FIG. 13A

FIG. 13B

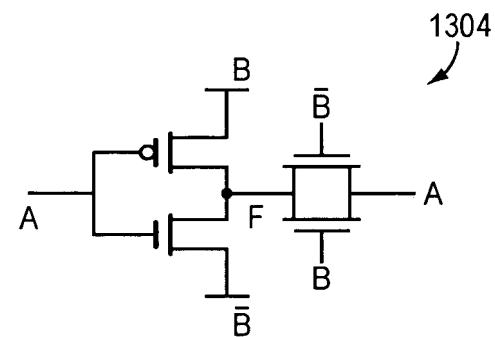


FIG. 13C